Abstracts

High Power Control Components Using a New Monolithic FET Structure

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A new monolithic switch FET (MFET) control device has been developed that can be integrated with other monolithic functions or used as a discrete component in a MMIC structure. This device increases the power handling capability of the conventional switch FET (SFET) by an order of magnitude. It does this by overcoming the breakdown voltage limitation of the SFET device. The design, fabrication, and performance of two high power control components using MFET devices are described as examples of the implementation of this technology (an L-Band terminated single pole single throw (SPST) switch, and an L-Band limiter).

❑ Return to main document.